



520.37698CX1

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): TAKAHASHI, et al.

Serial No.: 09/414,520 (CPA)

Filed: October 8, 1999

For: PLASMA PROCESSING APPARATUS AND A PLASMA
PROCESSING METHOD

Group: 1763

Examiner: Zervigon, R.

AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

June 19, 2002

Sir:

In response to the Office Action of February 19,
2002, please amend the application as follows:

IN THE CLAIMS

Please amend Claims 1 and 6 as follows:

DI

1. (four times amended) In a plasma processing apparatus for etching an electrically insulating film, the plasma processing apparatus having a vacuum processing chamber, a sample table for mounting a sample which is processed in said vacuum processing chamber, and a plasma generation means, wherein a plasma processing is carried out by generating a plasma in response to introduction of a gas

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FR ⇒ 10/12/02
USF ⇒ 10/18/02